

TC7WH241FU, TC7WH241FK

Dual Bus Buffer Non Inverted, 3-State Outputs

The TC7WH241 is an advanced high speed CMOS DUAL BUS BUFFERS fabricated with silicon gate CMOS technology.

They achieve the high speed operation similar to equivalent Bipolar Schottky TTL while maintaining the CMOS low power dissipation. The 7WH241 is an inverting 3-state buffer having two active-low output enables.

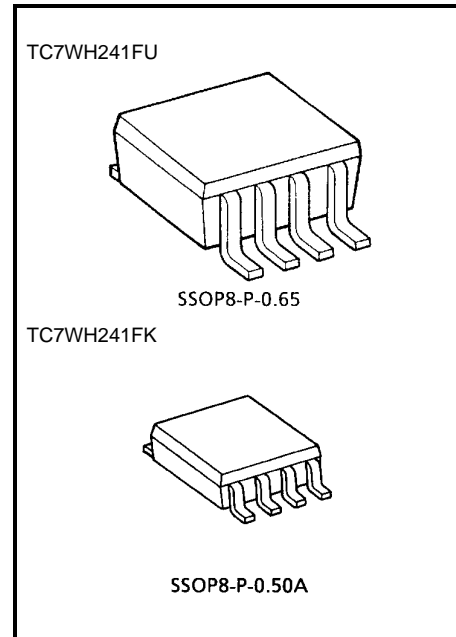
This device is designed to be used with 3-state memory address drivers, etc.

An input protection circuit ensures that 0 to 7 V can be applied to the input pins without regard to the supply voltage.

This device can be used to interface 5 V to 3 V systems and two supply systems such as battery back up. This circuit prevents device destruction due to mismatched supply and input voltages.

Features

- High speed: $t_{pd} = 3.6 \text{ ns (typ.)}$ at $V_{CC} = 5 \text{ V}$
- Low power dissipation: $I_{CC} = 2 \mu\text{A (max)}$ at $T_a = 25^\circ\text{C}$
- High noise immunity: $V_{NIH} = V_{NIL} = 28\% V_{CC} \text{ (min)}$
- 5.5-V Tolerant inputs.
- Balanced propagation delays: $t_{pLH} \approx t_{pHL}$
- Wide operating voltage range: $V_{CC} \text{ (opr)} = 2\text{--}5.5 \text{ V}$
- Low Noise : $V_{OLP} = 0.8 \text{ V (max.)}$

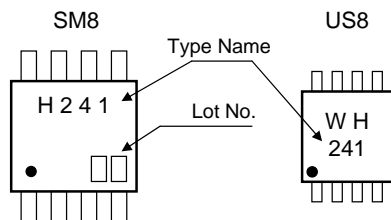


Weight

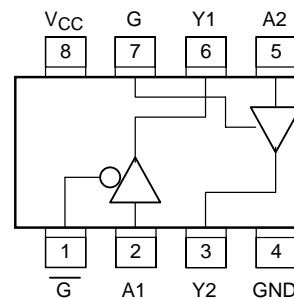
SSOP8-P-0.65: 0.02 g (typ.)

SSOP8-P-0.50A: 0.01 g (typ.)

Marking



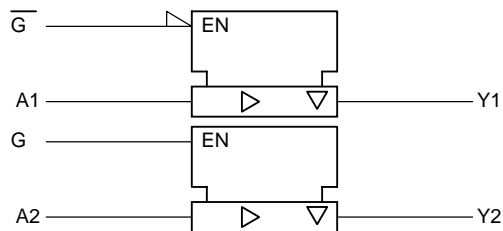
Pin Assignment (top view)



Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Supply voltage range	V _{CC}	-0.5~7.0	V
DC input voltage	V _{IN}	-0.5~7.0	V
DC output voltage	V _{OUT}	-0.5~V _{CC} + 0.5	V
Input diode current	I _{IK}	-20	mA
Output diode current	I _{OK}	±20	mA
DC output current	I _{OUT}	±25	mA
DC V _{CC} /ground current	I _{CC}	±50	mA
Power dissipation	P _D	300 (SM8)	mW
		200 (US8)	
Storage temperature	T _{stg}	-65~150	°C
Lead temperature (10 s)	T _L	260	°C

Logic Diagram



Truth Table

INPUTS			OUTPUTS
G-bar	G	A	Y-bar
L	H	L	L
L	H	H	H
H	L	X	Z

X : Don't Care

Z : High Impedance

Recommended Operating Conditions

Characteristics	Symbol	Rating	Unit
Supply voltage	V _{CC}	2.0~5.5	V
Input voltage	V _{IN}	0~5.5	V
Output voltage	V _{OUT}	0~V _{CC}	V
Operating temperature	T _{opr}	-40~85	°C
Input rise and fall time	dt/dv	0~100 (V _{CC} = 3.3 ± 0.3 V)	ns/V
		0~20 (V _{CC} = 5 ± 0.5 V)	

Electrical Characteristics

DC Characteristics

Characteristics	Symbol	Test Condition		Ta = 25°C			Ta = -40~85°C		Unit		
				V _{CC} (V)	Min	Typ.	Max	Min		Max	
High-level input voltage	V _{IH}	—		2.0	1.50	—	—	1.50	—	V	
				3.0~5.5	V _{CC} × 0.7	—	—	V _{CC} × 0.7	—		
Low-level input voltage	V _{IL}	—		2.0	—	—	0.50	—	0.50	V	
				3.0~5.5	—	—	V _{CC} × 0.3	—	V _{CC} × 0.3		
High-level output voltage	V _{OH}	V _{IN} = V _{IH} or V _{IL}		I _{OH} = -50 μA	2.0	1.9	2.0	—	1.9	—	V
					3.0	2.9	3.0	—	2.9	—	
					4.5	4.4	4.5	—	4.4	—	
				I _{OH} = -4 mA	3.0	2.58	—	—	2.48	—	
					4.5	3.94	—	—	3.80	—	
Low-level output voltage	V _{OL}	V _{IN} = V _{IH} or V _{IL}		I _{OL} = 50 μA	2.0	—	0.0	0.1	—	0.1	V
					3.0	—	0.0	0.1	—	0.1	
					4.5	—	0.0	0.1	—	0.1	
				I _{OL} = 4 mA	3.0	—	—	0.36	—	0.44	
					4.5	—	—	0.36	—	0.44	
3-State Output Off-State Current	I _{OZ}	V _{IN} = V _{IH} or V _{IL} V _{OUT} = V _{CC} or GND		5.5	—	—	0.25	—	2.50	μA	
Input leakage current	I _{IN}	V _{IN} = 5.5 V or GND		0~5.5	—	—	±0.1	—	±1.0	μA	
Quiescent supply current	I _{CC}	V _{IN} = V _{CC} or GND		5.5	—	—	2.0	—	20.0	μA	

AC Characteristics (Input: $t_r = t_f = 3$ ns)

Characteristics	Symbol	Test Condition			Ta = 25°C			Ta = -40~85°C		Unit
			V _{CC} (V)	C _L (pF)	Min.	Typ.	Max.	Min.	Max.	
Propagation Delay Time	t _{pLH}		3.3 ± 0.3	15	—	5.3	7.5	1.0	9.0	ns
				50	—	7.8	11.0	1.0	12.5	
	5.0 ± 0.5		15	—	3.6	5.5	1.0	6.5		
			50	—	5.1	7.5	1.0	8.5		
3-State Output Enable Time	t _{pZL}	R _L = 1kΩ	3.3 ± 0.3	15	—	6.6	10.6	1.0	12.5	ns
				50	—	9.1	14.1	1.0	16.0	
	5.0 ± 0.5		15	—	4.7	7.3	1.0	8.5		
			50	—	6.2	9.3	1.0	10.5		
3-State Output Disable Time	t _{pLZ}	R _L = 1kΩ	3.3 ± 0.3	50	—	10.3	14.0	1.0	16.0	ns
				50	—	6.7	9.2	1.0	10.5	
t _{pHZ}	5.0 ± 0.5		50	—	6.7	9.2	1.0	10.5		
			50	—	6.7	9.2	1.0	10.5		
Output to Output Skew	t _{osLH}	(Note 1)	3.3 ± 0.3	50	—	—	1.5	—	1.5	ns
				50	—	—	1.0	—	1.0	
t _{osHL}	5.0 ± 0.5		50	—	—	1.0	—	1.0		
			50	—	—	1.0	—	1.0		
Input Capacitance	C _{I/N}				—	4	10	—	10	pF
Output Capacitance	C _{I/O}				—	6	—	—	—	pF
Power Dissipation Capacitance (Note 2)	C _{PD}				—	17	—	—	—	pF

Note 1 : Parameter guaranteed by design.

$$t_{osLH} = |t_{pLHm} - t_{pLHn}|, \quad t_{osHL} = |t_{pHLm} - t_{pHLn}|$$

Note 2: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

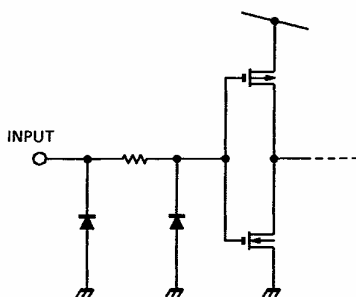
Average operating current can be obtained by the equation :

$$I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/2$$

Noise Characteristics (Ta = 25°C, input: $t_r = t_f = 3$ ns)

Characteristics	Symbol	Test Condition	V _{CC} (V)	Typ.	Limit	Unit
Quiet output minimum dynamic V _{OL}	V _{OLV}	C _L = 50 pF	5.0	-0.3	-0.8	V
Minimum high level dynamic input voltage	V _{IHD}	C _L = 50 pF	5.0	—	3.5	V
Maximum low level dynamic input voltage	V _{ILD}	C _L = 50 pF	5.0	—	1.5	V

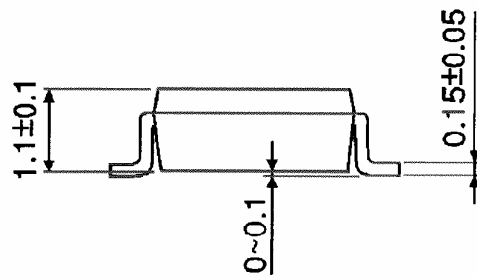
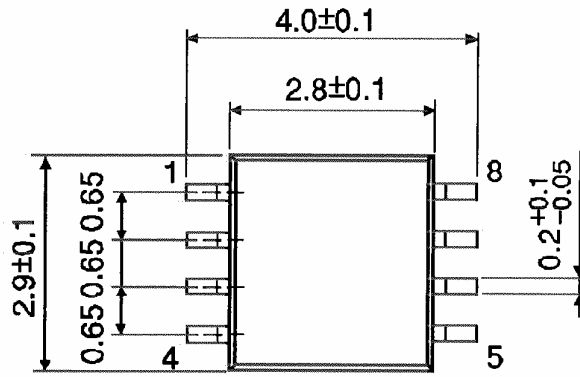
Input Equivalent Circuit



Package Dimensions

SSOP8-P-0.65

Unit : mm

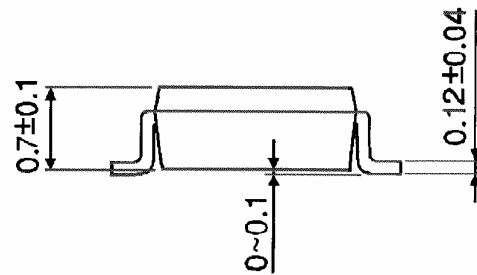
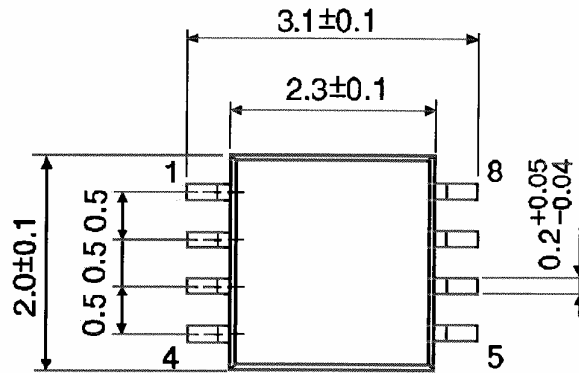


Weight: 0.02 g (typ.)

Package Dimensions

SSOP8-P-0.50A

Unit : mm



Weight: 0.01 g (typ.)

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